



RapidRF Smart LDMOS前端设计

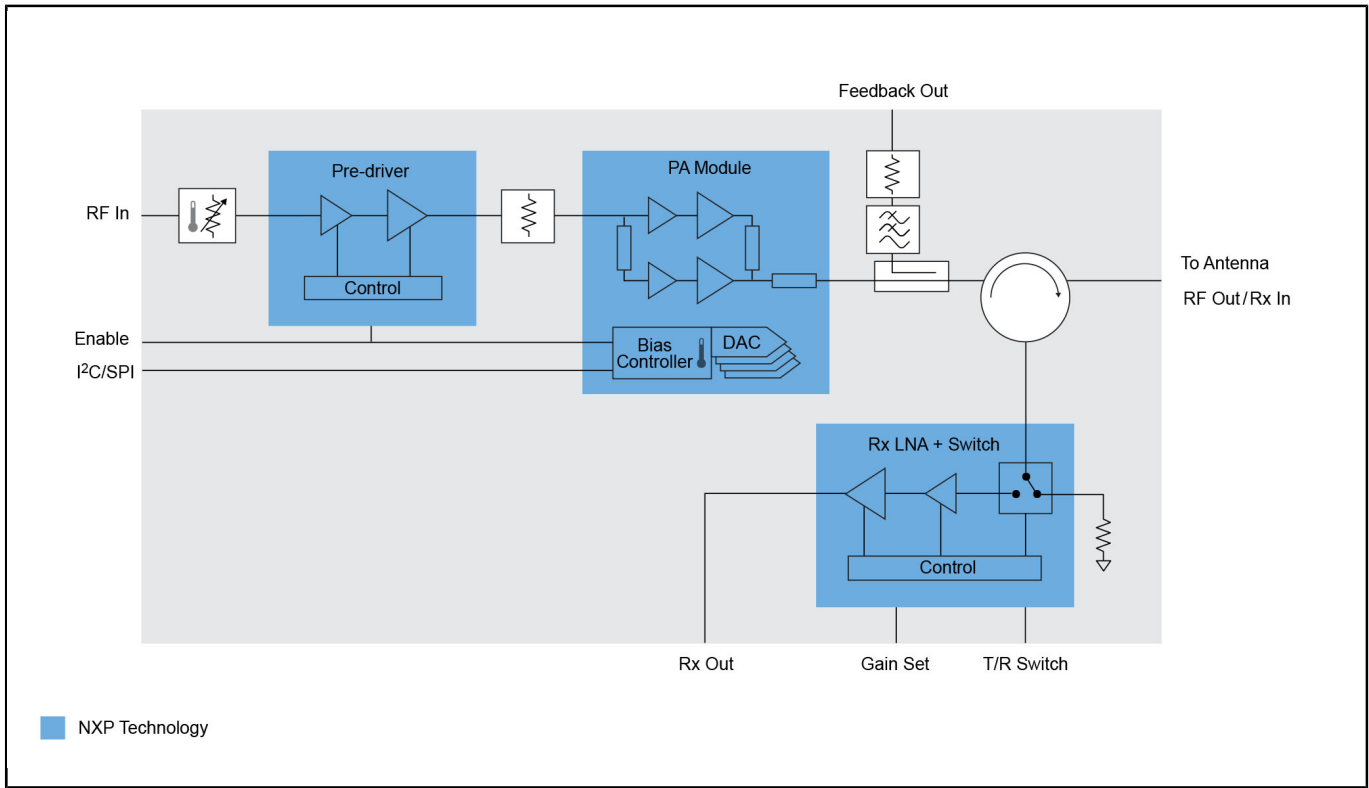
RAPIDRFSL-FRONTEND

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恩智浦的RapidRF Smart LDMOS前端设计进一步集成了高效射频功率放大器、线性预驱动器、带T/R开关的Rx LNA和循环器，整合在紧凑的封装中，同时功率放大器封装中包含偏置控制器和温度传感器。设计包含用于DPD反馈的耦合器，并将与数字预失真一起使用。

对于要求天线平均发射功率为2.5至8瓦（34-39 dBm）的5G射频单元，RapidRF参考板是上佳选择。通用PCB布局用于多个频段，简化了设计和制造，加快了产品面市速度。

RapidRF Smart LDMOS前端结构框图 Block Diagram



View additional information for [RapidRF Smart LDMOS前端设计](#).

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